



Air Force Invention No. AFB00670

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On 23 March 2004
(DATE OF DEPOSIT)

WILLIAM G. AUTON 31,320
NAME OF APPLICANT, ASSIGNEE, OR REG. REP.


23 March 2004
SIGNATURE DATE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of
Richard A. Soref et al
Application Serial No. 10/722,611
Filed: 28 November 2003
For: Strain-engineered Direct-Gap Ge/Sn_xGe_{1-x} Heterodiode and Multi-Quantum-Well Photodetectors, Lasers, Emitters and Modulators grown on Sn_ySi_zGe_{1-y-z}-buffered Silicon

Honorable Commissioner of Patents and Trademarks
Washington D. C. 20231-0001

Sir:

RESPONSE TO NOTICE TO FILE CORRECTED APPLICATION PAPERS

In response to the Office Action of 27 February 2004, please consider the following amendment. A fee of \$130 is enclosed.

IN THE CLAIMS

Please retain all original claims.

04/07/2004 SZENDIE1 00000007 010465 10772611

01 FC:1460 130.00 DA

05/24/2004 JMCMILLA 00000003 010465 10772611

01 FC:1203 290.00 DA